

2225-4L

3.5 Watts, 24 Volts, Class C Microwave 2200-2500 MHz

The 2225-4 Class C outp input prema diffused bal ruggedness. Sealed pack	0	Hz. The transistor includes Gold metalization and ility and supreme Iigh Temperature Solder	CASE OUTLINE 55LV, STYLE 1
ABSOI	LUTE MAXIMUM RA'	TINGS	
Maximum Power Dissipation @ 25°C 10 Watts		10 Watts	
BVces BVebo Ic <b>Maximum</b> Storage Ten	Voltage and Current Collector to Emitter Voltage Emitter to Base Voltage Collector Current Temperatures nperature unction Temperature	40 Volts 3.5 Volts 0.6 Amps - 65 to + 200°C + 200°C	

## ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Pout Pin Pg ηc VSWR	Power Out Power Input Power Gain Efficiency Load Mismatch Tolerance	F = 2200-2500 MHz Vcc = 24 Volts Pout =3.5Watts	3.5 8.5	40	0.5 10:1	Watts Watts dB %

BVces BVebo Hfe Cob θjc	Collector to Emitter Breakdown Emitter to Base Breakdown Current Gain Output Capacitance Thermal Resistance	Ic = 10 mA Ie = 5 mA Vce = 5V, Ic = 200 mA Vcb = 24 F = 1 MHz Tc = $25^{\circ}$ C	40 3.5 20	7	120 17.0	Volts Volts pF °C/W	
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